TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP621,TLP621-2,TLP621-4

Programmable Controller
AC / DC-Input Module
Solid State Relay

The TOSHIBA TLP621, -2 and -4 consists of a photo–transistor optically coupled to a gallium arsenide infrared emitting diode. The TLP621–2 offers two isolated channels in an eight lead plastic DIP, which the TLP621–4 provides four isolated channels in a sixteen plastic DIP

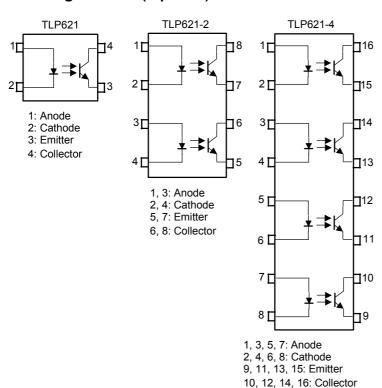
• Collector-emitter voltage: 55 V (min.)

• Current transfer ratio: 50% (min.)

Rank GB: 100% (min.)

Weight: 0.26 g

Pin Configurations (top view)



TLP621-2

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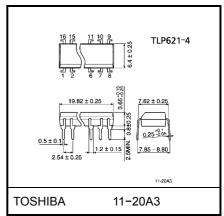
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Weight: 1.1 g

• Current Transfer Ratio

Туре	Type $Classi (\%) (I_C / I_F)$ $I_F = 5mA, V_{CE} = 5V, Ta = 25^{\circ}C$ $Min.$ Max		Marking Of Classification	
	(None)	50	600	Blank, Y, Y [*] , G, G [*] , B, B [*] , GB
	(None)	30	000	Blatik, 1, 1, O, O, B, B, OB
	Rank Y	50	150	Y, Y*
TLP621	Rank GR	100	300	G, G [■]
	Rank BL	200	600	B, B ■
	Rank GB	100	600	G, G*, B, B*, GB
TLP621-2	(None)	50	600	Blank, GR, BL, GB
TLP621-4	Rank GB	100	600	GR, BL, GB

^{*1:} Ex. rank GB: TLP621 (GB)

(Note) Application type name for certification test, please use standard product type name, i.e.

TLP621 (GB): TLP621 TLP621-2 (GB): TLP621-2

	Made In Japan	Made In Thailand		
UL recognized	E67349	*2	E152349 *.	2
BSI approved	6508, 7445	*3	6505, 7445 *	3
SEMKO approved	9735090 / 01	*4	1	

- *2 UL1577
- *3 BS EN60065: 1994, BS EN60950: 1992
- *4 EN60950 (approved is TLP621 only)

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• Option (D4) type

VDE approved: DIN VDE0884 / 06.92, certificate no. 68384

 $\label{eq:maximum operating insulation voltage: 890 VPK} \\ Highest permissible over voltage: 8000 VPK \\$

(Note) When a VIDE0884 approved type is needed, please disignate the "Option (D4)"

		7.62 mm pich	10.16 mm pich
		standard type	(LF2) type
•	Creepage distance	: 6.4 mm (min.)	8.0 mm (min)
	Clearance	: 6.4 mm (min.)	8.0 mm (min)
	Insulation thickness	: 0.4 mm (min.)	0.4 mm (min)



Maximum Ratings (Ta = 25°C)

			Ra	ting			
	Characteritic	Symbol	TLP621	TLP621-2 TLP621-4	Unit		
	Forward current	l _F	60	50	mA		
	Forward current derating	ΔI _F /°C	−0.7 (Ta > 39°C)	−0.5 (Ta = 25°C)	mA /°C		
	Pulse forward current	I _{FP}	1 (100µs pu	lse, 100pps)	Α		
LED	Power dissipation	P _D	100	70	mW		
	Power dissipation derating	ΔP _D /°C	-1.0	-0.7	mW /°C		
	Reverse voltage	V _R	Į.	5	V		
	Junction temperature	Tj	12	125			
	Collector-emitter voltage	V _{CEO}	5	V			
	Emitter-collector valtage	V _{ECO}	-	V			
'n	Collector current	Ic	5	mA			
Detector	Collector power dissipation (1 circuit)	P _C	150	100	mW		
	Collector power dissipation derating (1 circuit, Ta ≥ 25°C)	ΔP _C /°C	-1.5	-1.0	mW /°C		
	Junction temperature	Tj	12	25	°C		
Stor	rage temperature range	T _{stg}	-55~125		°C		
Оре	erating temperature range	T _{opr}	−55 ~ 100		°C		
Lead soldering temperature		T _{sol}	260 (10 s)		°C		
Total package power dissipation		PT	250 150		mW		
Total package power dissipation derating (Ta ≥ 25°C)		ΔP _T /°C	-2.5 -1.5		mW /°C		
Isola	ation voltage (Note 1)	BVS	5000 (AC, 1mi	n., R.H.≤ 60%)	V _{rms}		

(Note 1) Device considered a two terminal: LED side pins shorted together, and detector side pins shorted together.

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Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{CC}	_	5	24	V
Forward current	I _F	_	16	20	mA
Collector current	IC	_	1	10	mA
Operating temperature	T _{opr}	-25	-	85	°C



Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
LED	Reverse current	I _R	V _R = 5 V	_	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	_	pF
	Collector–emitter breakdown voltage	V _(BR) CEO	I _C = 0.5 mA	55	_	_	V
ctor	Emitter-collector breakdown voltage	V _{(BR) ECO}	I _E = 0.1 mA	7	_	_	V
Detector	Collector dark current	ICEO	V _{CE} = 24 V	_	10	100	nA
			V _{CE} = 24 V, Ta = 85°C	_	2	50	μΑ
	Capacitance (collector to emitter)	C _{CE}	V = 0, f = 1 MHz		10	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	MIn.	Тур.	Max.	Unit
Current transfer ratio	I _C / I _F	I _F = 5 mA, V _{CE} = 5 V	50	_	600	%
		Rank GB	100	_	600	70
Saturated CTR	I _C / I _{F (sat)}	I_F = 1 mA, V_{CE} = 0.4 V Rank GB	_	60	_	- %
Saturated CTR			30	_	_	70
		I _C = 2.4 mA, I _F = 8 mA	_	_	0.4	
Collector–emitter saturation voltage	V _{CE} (sat)	I _C = 0.2 mA, I _F = 1 mA	_	0.2	_	V
		Rank GB	_	_	0.4	

Isolation Characteristics (Ta = 25°C)

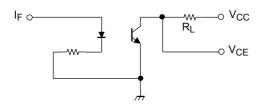
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	CS	V _S = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V	1×10 ¹²	10 ¹⁴	_	Ω
Isolation voltage		AC, 1 minute	5000	_	_	\/
		AC, 1 second, in oil	_	10000	_	V _{rms}
		DC, 1 minute, in oil	_	10000	_	V_{dc}

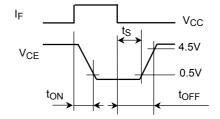


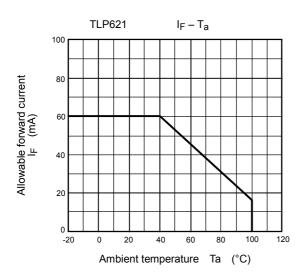
Switching Characteristics (Ta = 25°C)

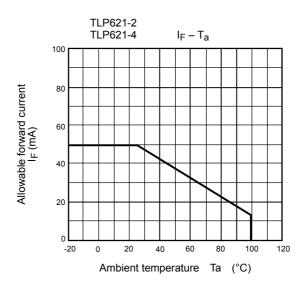
Characterictic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t _r	V_{CC} = 10 V, I _C = 2 mA R _L = 100 Ω	_	2	_	
Fall time	t _f		_	3	_	116
Turn-on time	t _{on}		1	3	_	μs
Turn-off time	t _{off}		_	3	_	
Turn-on time	t _{ON}	$R_L = 1.9 \text{ k}\Omega \text{ (Fig.1)}$ $V_{CC} = 5 \text{ V, I}_F = 16 \text{ mA}$	_	2	_	
Storage time	t _S		_	15	_	μs
Turn-off time	t _{OFF}		_	25	_	

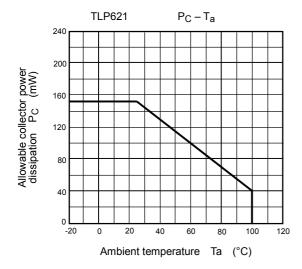
Fig. 1 Switching time test circuit

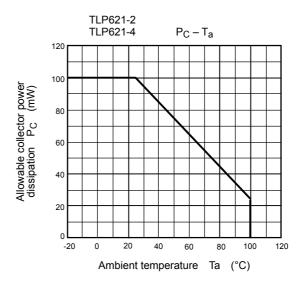


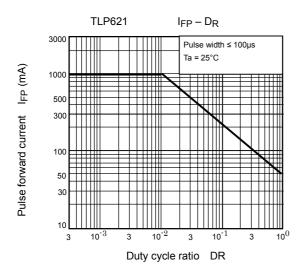


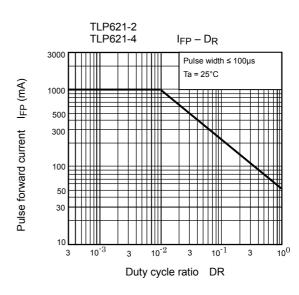


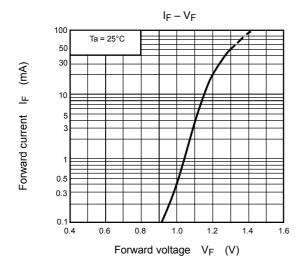


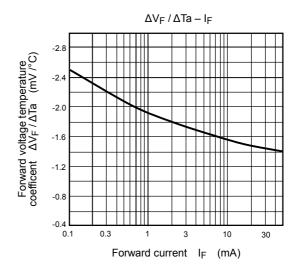


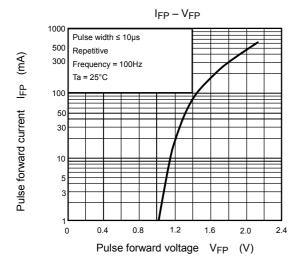


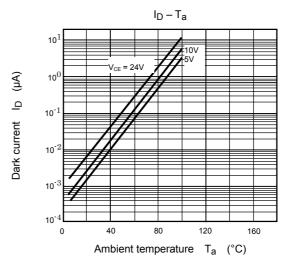


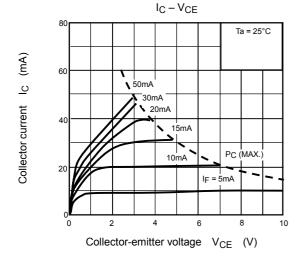


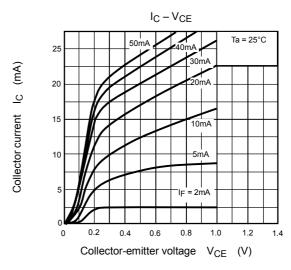


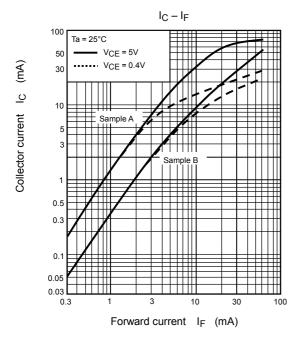


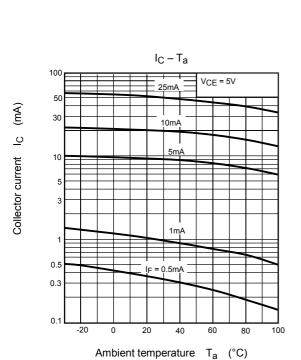


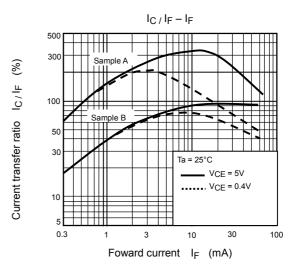


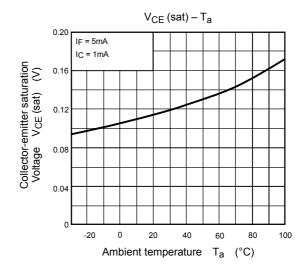


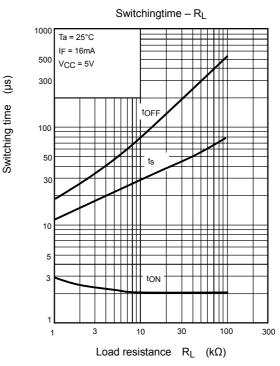












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